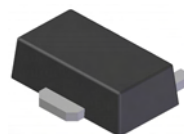


Features

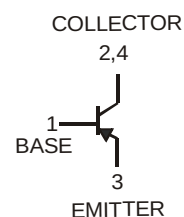
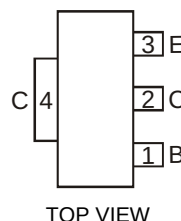
- Epitaxial Planar Die Construction
- Complementary NPN Type Available (DXT2222A)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free by Design/RoHS Compliant (Note 1)**
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams



SOT89-3L



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-60	V
Collector-Base Voltage	V _{CBO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-600	mA
Peak Collector Current	I _{CM}	-800	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	R _{θJA}	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-60	—	V	I _C = -10μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60	—	V	I _C = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5.0	—	V	I _E = -10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	-10	nA μA	V _{CB} = -50V, I _E = 0 V _{CB} = -50V, I _E = 0, T _A = 150°C
Collector Cutoff Current	I _{CEX}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -0.5V
Emitter Cutoff Current	I _{EBO}	—	-50	nA	V _{EB} = -5V, I _C = 0
Base Cutoff Current	I _{BL}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -0.5V
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h _{FE}	75 100 100 100 50	— — — 300 —	—	I _C = -100μA, V _{CE} = -10V I _C = -1.0mA, V _{CE} = -10V I _C = -10mA, V _{CE} = -10V I _C = -150mA, V _{CE} = -10V I _C = -500mA, V _{CE} = -10V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.4 -1.6	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	-1.3 -2.6	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	8.0	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	30	pF	V _{EB} = -2.0V, f = 1.0MHz, I _C = 0
Current Gain-Bandwidth Product	f _T	200	—	MHz	V _{CE} = -20V, I _C = -50mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Turn-On Time	t _{on}	—	45	ns	V _{CC} = -30V, I _C = -150mA, I _{B1} = -15mA
Delay Time	t _d	—	10	ns	
Rise Time	t _r	—	40	ns	
Turn-Off Time	t _{off}	—	100	ns	V _{CC} = -6.0V, I _C = -150mA, I _{B1} = I _{B2} = -15mA
Storage Time	t _s	—	80	ns	
Fall Time	t _f	—	30	ns	

Notes: 4. Short duration pulse test used to minimize self-heating effect.

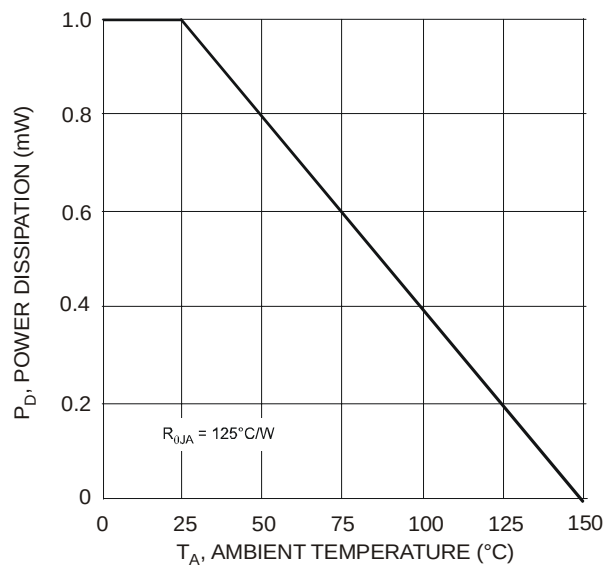


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

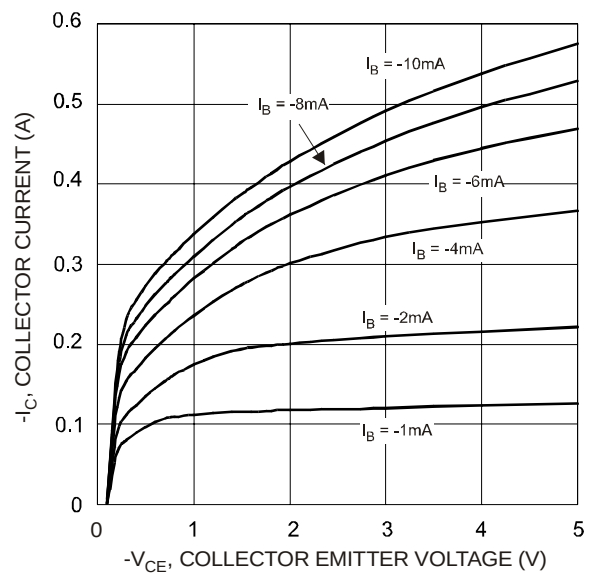


Fig. 2 Typical Collector Current as a Function of Collector Emitter Voltage

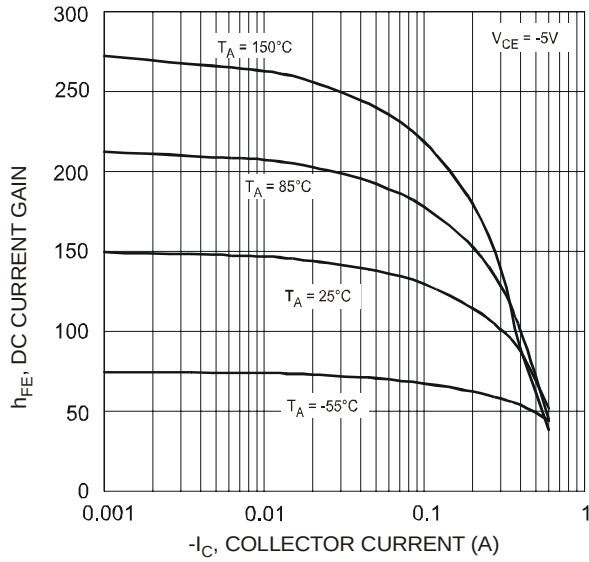


Fig. 3 Typical DC Current Gain vs. Collector Current

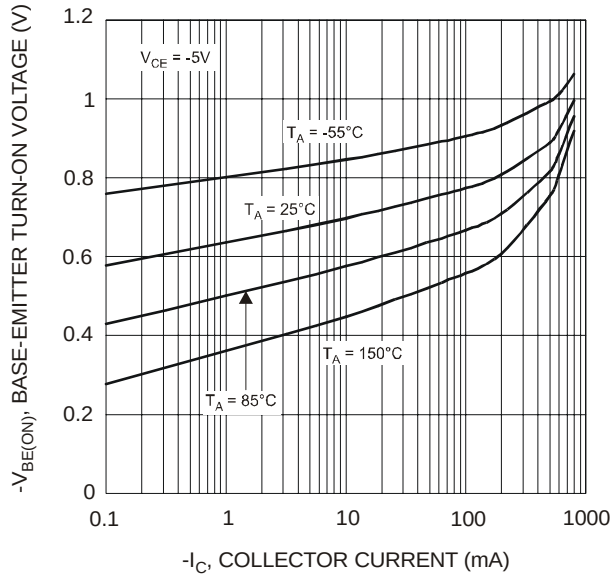


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

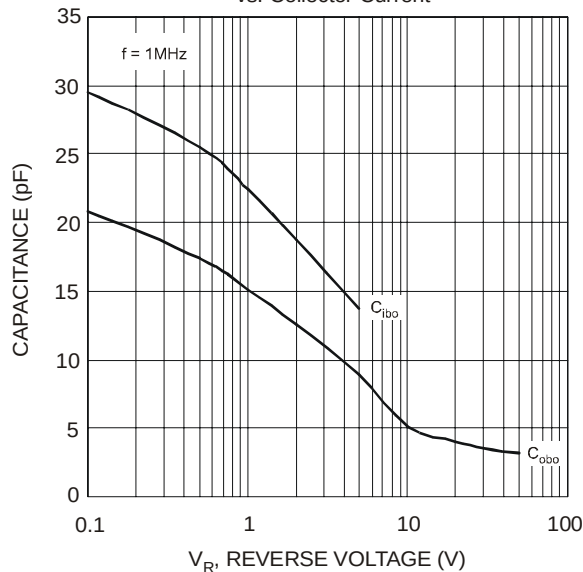


Fig. 7 Typical Capacitance Characteristics

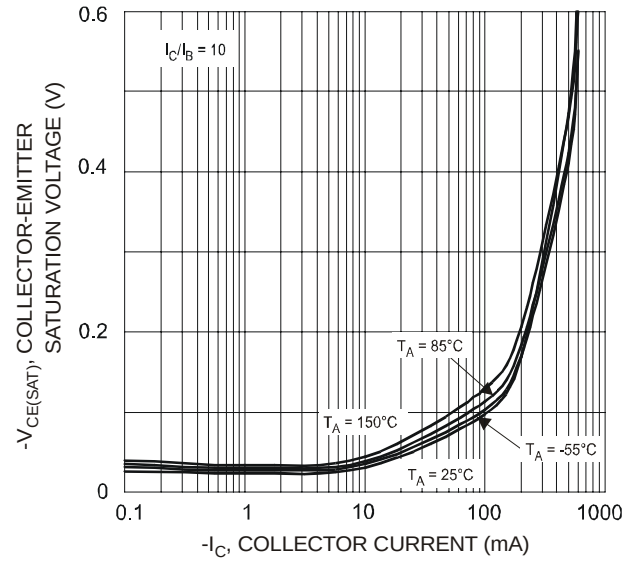


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

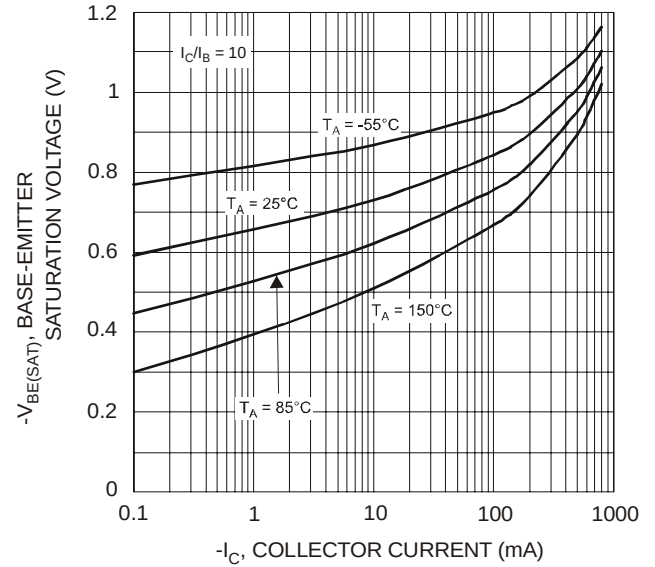


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

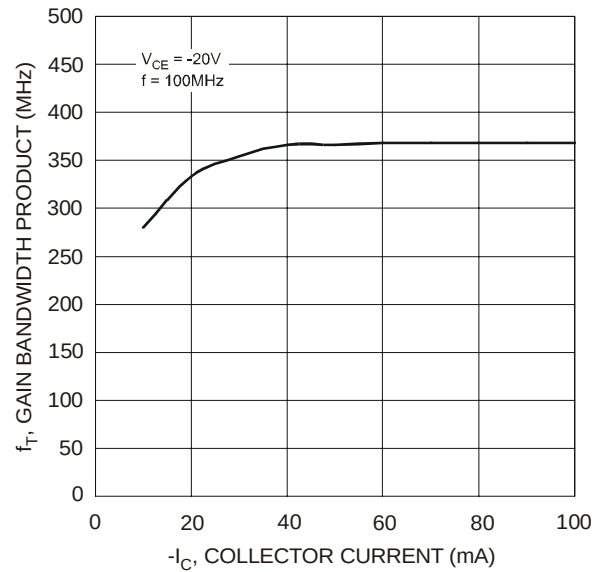


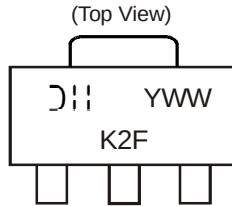
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DXT2907A-13	SOT89-3L	2500/Tape & Reel

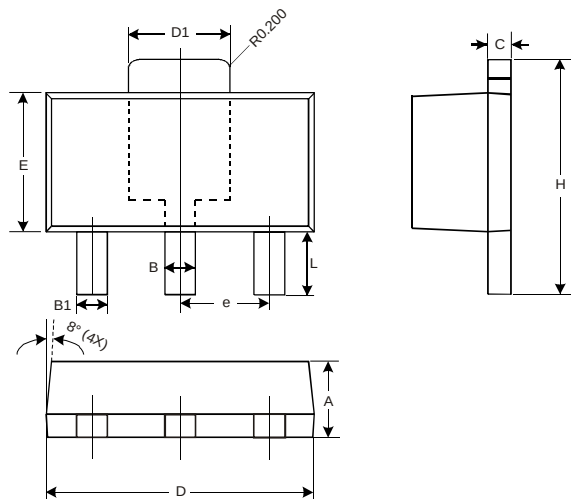
Notes: 5. For packaging details go to our website at <http://www.diodes.com/ap2007.pdf>.

Marking Information



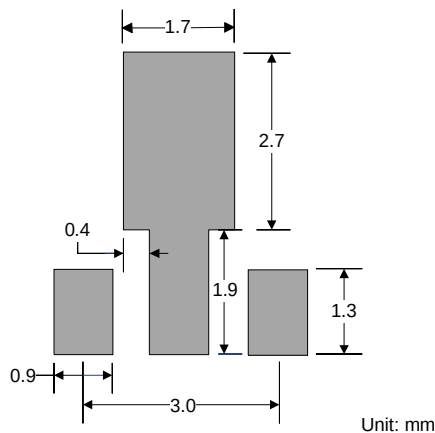
011 = Manufacturer's code marking
 K2F = Product Type Marking Code
 YWW = Date Code Marking
 Y = Last digit of year ex: 7 = 2007
 WW = Week code 01 - 52

Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	0.160	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

Suggested Pad Layout



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